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In the Specification:**Please amend paragraph [0003] as follows:**

- B1
- [0003] Such a III nitride film is formed as follows. First of ~~all~~, a buffer film is formed ~~off~~from a III nitride material on a substrate made of a single crystal material, and an underlayer is formed ~~off~~from a III nitride material on the buffer film. Then, one or more III nitride films having their respective functions are formed on the underlayer, to fabricate a semiconductor element such as a light-emitting diode. Generally, the substrate, and the buffer film and the underlayer are combined, and called as an "epitaxial substrate".

Please amend paragraph [0005] as follows:

- B2
- [0005] Practically, if the buffer film is made of AlN, the warpage of the epitaxial substrate is increased up to 70 μm , and thus, in the manufacturing process of semiconductor elements encompassing various semiconductor films formation processes, the photolithography process can not be performed precisely, so that the manufacturing yield ratio of semiconductor element can be deteriorated.

Please amend paragraph [0008] as follows:

- B3
- [0008] Also, this invention relates to an ~~epitaxial~~epitaxial substrate comprising:
a base made of a single crystal material,
a III nitride buffer film including at least Al element and having a screw-type dislocation density of $1 \times 10^8/\text{cm}^2$ or below which is formed on said base, and
a III nitride underfilm which is formed on said III nitride buffer film.

Please amend paragraph [0010] as follows:

- B4
- [0010] In the past, a buffer film of an epitaxial substrate is formed at a lower temperature within 500-700°C so as to mitigate the difference in lattice constant between a substrate and an underfilm, and thus, enhance the buffer effect. Therefore, the crystal quality may be degraded to some degree, and ~~much~~large dislocation of a density of $10^9/\text{cm}^2$ or ~~over~~more may be created therein.

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Please amend paragraph [0013] as follows:

B5

[0013] The present invention is achieved by the prominent attention of the inventors which breaks down a conventional ideas.

Please amend paragraph [0015] as follows:

B6

[0015] Therefore, in the lithograph step of the manufacturing process of a semiconductor element, a multilayered substrate of e.g., a base substrate, a buffer film and an underlayer can be set to a desired position precisely, so the lithograph step can be performed precisely. As a result, the manufacturing yielding ratio of the semiconductor element can be developed remarkably.

Please amend paragraph [0016] as follows:

B7

[0016] The term "warpage" means a "warpage amplitude" of a multilayered structure such as an epitaxial base substrate and an epitaxial substrate if the multilayered structure is warped convexly or concavely, as shown in Fig. 1, and a "maximum warpage amplitude" thereof if the multilayered structure is warped in a wave shape.

Please amend the heading on page 3, line 19 as follows:

Detailed Description of the Invention~~Preferred Embodiments~~

Please amend paragraph [0023] as follows:

B8

[0023] The buffer film may include other III elements such as Ga element and In element, in addition to Al element. Also, the buffer film may include an additive element such as Ge, Si, Mg, Zn, Be, P or B as occasion demands, and a minute impurity such as O or C contained in the raw material gases and the reactor or contained dependent on the forming condition.